

参数 (Parameter)	符号 (Symbol)	单位(Uint)	测试条件(Condition)			M850
			Freq.	Fluxden.	Temp.	
初始磁导率 (Initial lPermeability)	μ_i	/	1000kHz	100mV	23°C	85±10%
Q (Q-Fator)	Q	/	1000kHz	100mV	23°C	30
磁通密度 (Flux Density)	Bm	mT	50Hz	20000A/m	23°C	1370
					100°C	1370
剩磁 (Residual Flux Density)	Br	mT	50Hz	20000A/m	23°C	60
					100°C	60
矫顽力 (Coercivity)	Hc	A/m	50Hz	20000A/m	23°C	500
					100°C	500
单位体积磁芯损失 (Core loss volume density)	Pcv	KW/m ³	100kHz	100mT	23°C	1150
绝缘阻抗 (Insulation)		MΩ		50V	23°C	1
密度 (Density)	d	g/cm ³				6.8

说明:以上性能采用 $\varnothing 10 \times \varnothing 6 \times 3$ 磁环, 在不加外力的情况下测试, 不同产品在特性表现上略有差异。

Note:Measured on sintered, non-ground ring cores of dimensions $\varnothing 10 \times \varnothing 6 \times 3$ which are not subjected to external stresses. Product specification will differ from these data due to the influence of geometry and size.

